



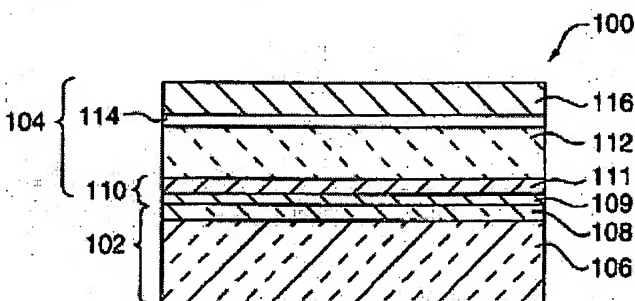


BEST AVAILABLE COPY**Ferroelectric device with capping layer and method of make same****Publication number:** CN1338113**Publication date:** 2002-02-27**Inventor:** SHINICHIRO HAYASHI (US);
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CARLOS A PAZ DE (US)**Applicant:** SYMETRIX CORP (US)**Classification:****- international:** *H01L21/02; H01L21/316;
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H01L21/316***- european:** H01L21/02B3B2; H01L21/316D**Application number:** CN19998016432 19991015**Priority number(s):** US19990229883 19990114**Also published as:** WO0042643 (A1)
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A ferroelectric device includes a ferroelectric layer and an electrode. The ferroelectric material is made of a perovskite or a layered superlattice material. A superlattice generator metal oxide is deposited as a capping layer between said ferroelectric layer and said electrode to improve the residual polarization capacity of the ferroelectric layer.

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